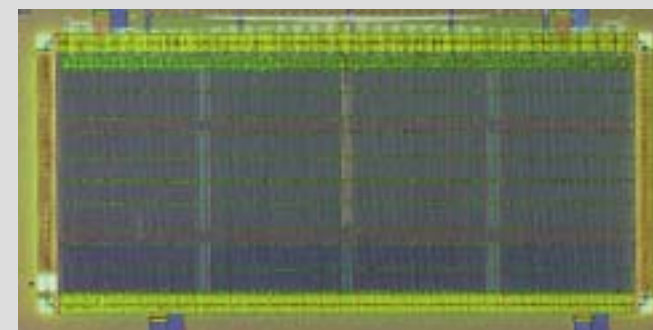
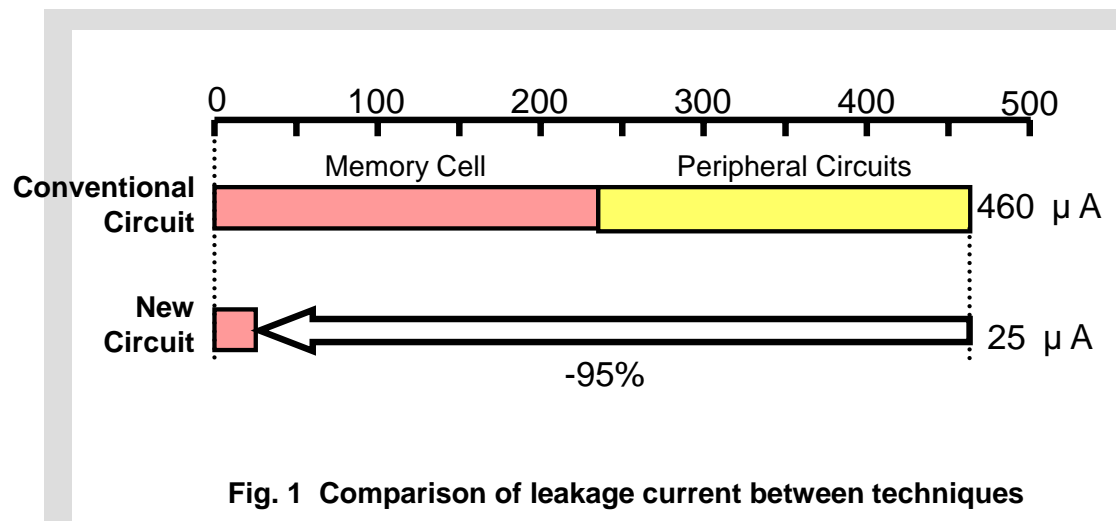


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Development of an on-chip SRAM circuit featuring the world's lowest standby current of 25 $\mu\text{A}/\text{Mbit}$ and 90% reduction in leakage current under low-speed operation



Hitachi, Ltd., in collaboration with Renesas Technology Corp. and SuperH, Inc., have developed new SRAM (static random-access memory) circuit technology for application in on-chip memory for SoCs used in cellular phones. The new circuit techniques developed achieved the world's lowest standby current of 25 $\mu\text{A}/\text{Mbit}$ and a reduction in leakage current to one-tenth of the conventional level under low-speed operation. For applications that require both high-performance processing and low power consumption, such as prolonged viewing of digital terrestrial broadcasts on cellular phones, this circuit technology significantly reduces power consumption by the SoCs.